

**UTT2523**

Preliminary

POWER MOSFET**-1.0A, -150V P-CHANNEL
POWER MOSFET****■ DESCRIPTION**

The UTC **UTT2523** is a P-channel MOS Field Effect Transistor. it uses UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance.

The UTC **UTT2523** is suitable for high voltage switching applications.

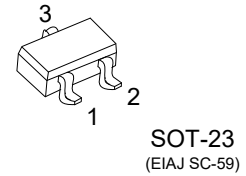
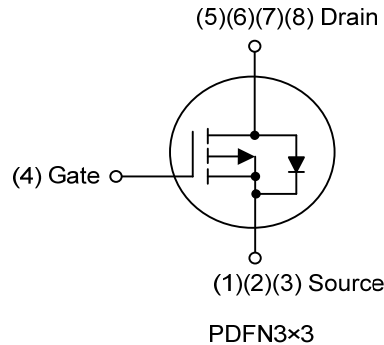
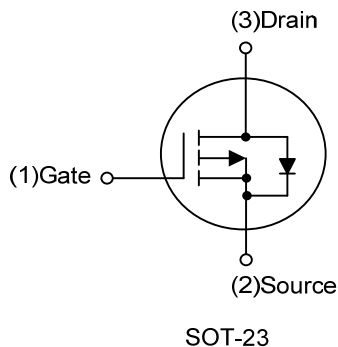
■ FEATURES

* $R_{DS(ON)} \leq 1.2 \Omega$ @ $V_{GS} = -10V$, $I_D = -0.5A$

$R_{DS(ON)} \leq 1.3 \Omega$ @ $V_{GS} = -6.0V$, $I_D = -0.5A$

* High switching speed

* Low input capacitance

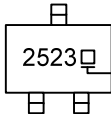
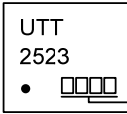
■ SYMBOL**■ ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTT2523L-AE3-R	UTT2523G-AE3-R	SOT-23	G	S	D	-	-	-	-	-	Tape Reel
UTT2523L-P3030-R	UTT2523G-P3030-R	PDFN3x3	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UTT2523G-AE3-R (1) Packing Type (2) Package Type (3) Green Package		(1) R: Tape Reel (2) AE3: SOT-23, P3030: PDFN3x3 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

SOT-23	PDFN3×3
 2523 □ → L: Lead Free G: Halogen Free	 UTT 2523 • □□□□ → Date Code

■ **ABSOLUTE MAXIMUM RATING** ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	-150	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	DC	I_D	-1	A
	Pulsed (Note 2)	I_{DM}	-1.6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	3.2	mJ
Power Dissipation ($T_A=25^{\circ}\text{C}$)	SOT-23	P_D	0.75	W
	PDFN3×3		1.67	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 20\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-23	θ_{JA}	166	$^{\circ}\text{C/W}$
	PDFN3×3		75	$^{\circ}\text{C/W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

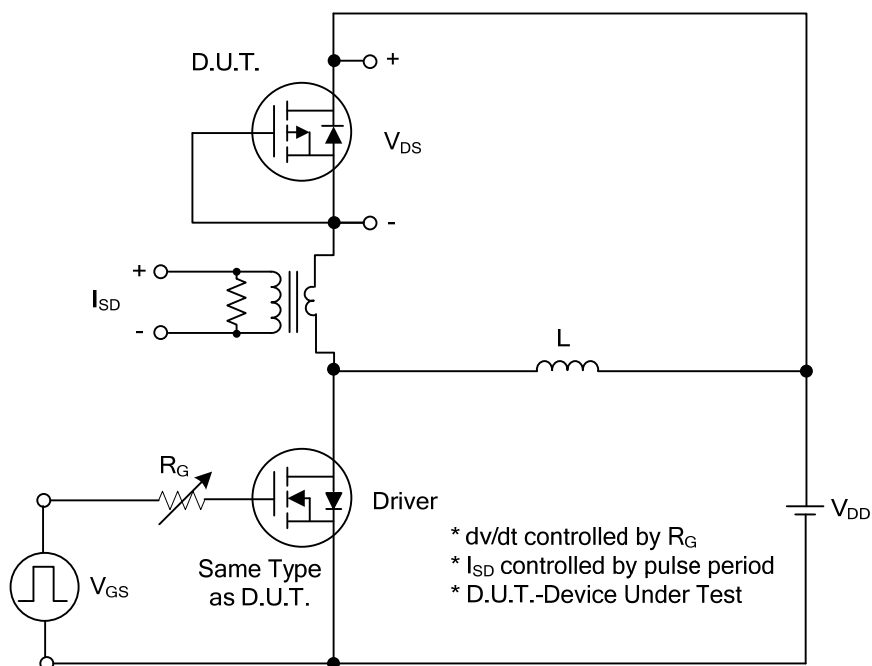
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =-250μA	-150			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-150V, V _{GS} =0V			-1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+10	μA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D =-250μA	-2.0		-4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =-10V, I _D =-0.5A			1.2	Ω
			V _{GS} =-6.0V, I _D =-0.5A			1.3	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =-25V, f=1.0MHz		300		pF
Output Capacitance		C _{OSS}			27		pF
Reverse Transfer Capacitance		C _{RSS}			14.5		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DS} =-75V, V _{GS} =-10V, I _D =-0.5A, I _D =-1mA (Note 1, 2)		11		nC
Gate to Source Charge		Q _{GS}			3		nC
Gate to Drain Charge		Q _{GD}			2		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DS} =-25V, V _{GS} =-10V, I _D =-0.5A, R _G =25Ω (Note 1, 2)		10		ns
Rise Time		t _R			17		ns
Turn-OFF Delay Time		t _{D(OFF)}			31		ns
Fall-Time		t _F			23		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				-1	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				-1.6	A
Diode Forward Voltage		V _{SD}	I _F =-1A, V _{GS} =0V			-1.2	V
Body Diode Reverse Recovery Time		t _{rr}	I _F =-1A, V _{GS} =0V, di/dt=100A/μs		32		ns
Body Diode Reverse Recovery Charge		Q _{rr}			36		nC

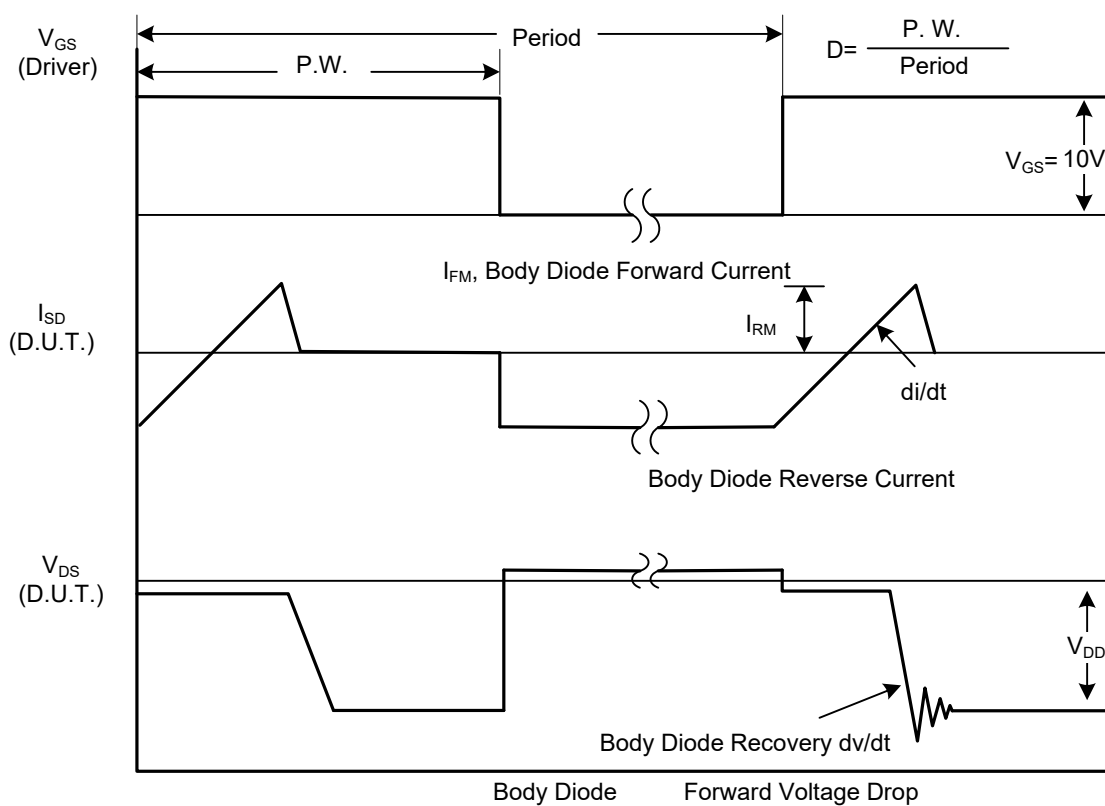
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

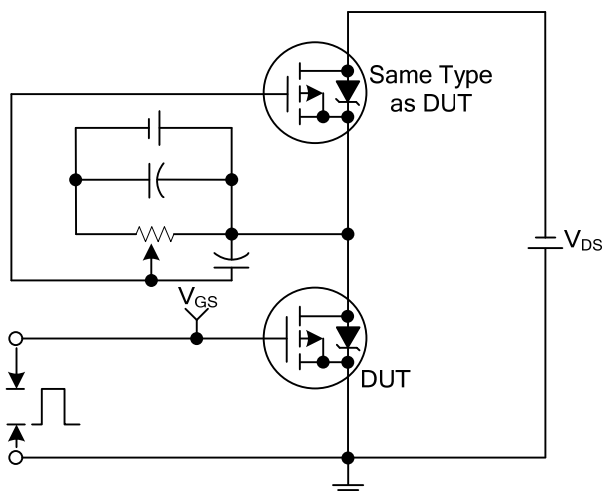


Peak Diode Recovery dv/dt Test Circuit

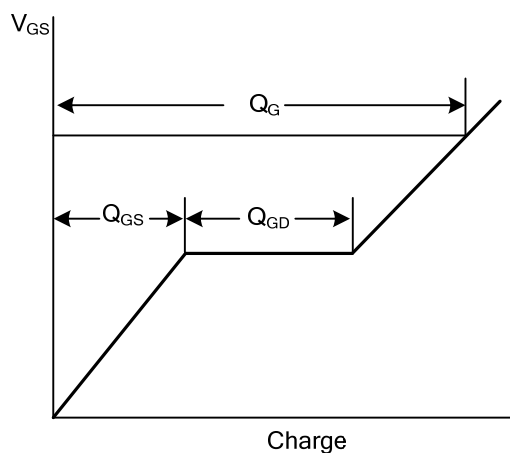


Peak Diode Recovery dv/dt Waveforms

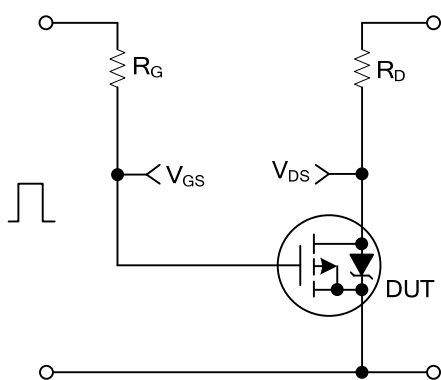
■ TEST CIRCUITS AND WAVEFORMS



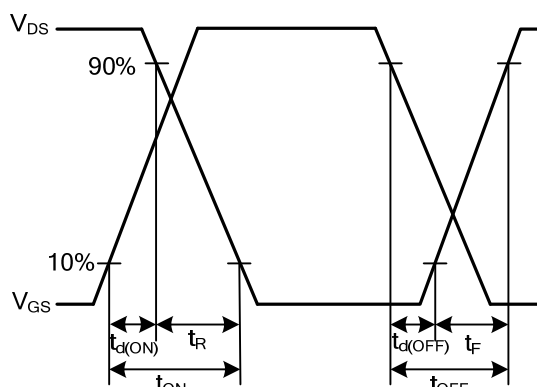
Gate Charge Test Circuit



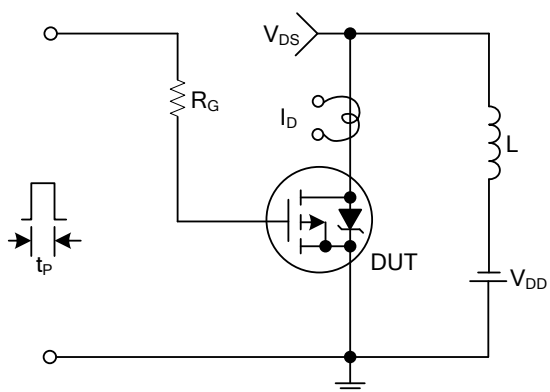
Gate Charge Waveforms



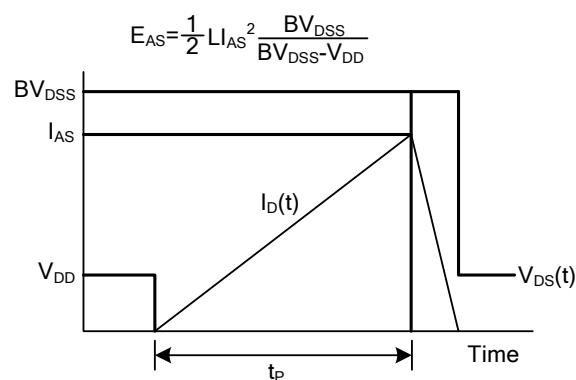
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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